AON3613

30V Complementary MOSFET

General Description

The AON3613 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used in inverter and other applications.

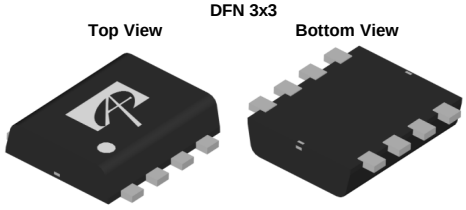
Product Summary

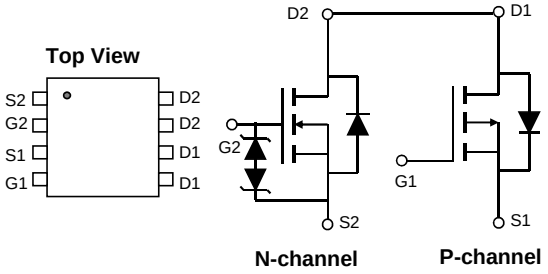
N-channel	P-channel	
V_{DS} (V) = 30V	V_{DS} (V) = -30V	
I_D = 4.5A	I_D = -4.5A	(V_{GS} = ±10V)
$R_{DS(ON)}$ < 52mΩ	$R_{DS(ON)}$ < 68mΩ	(V_{GS} = ±10V)
$R_{DS(ON)}$ < 60mΩ	$R_{DS(ON)}$ < 100mΩ	(V_{GS} = ±4.5V)

ESD protection
HBM Class 3A

Green Product

DFN 3x3





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Max N-channel	Max P-channel	Units
Drain-Source Voltage		V_{DS}	30	-30	V
Gate-Source Voltage		V_{GS}	±12	±20	V
Continuous Drain Current	T_A=25°C	I_D	4.5	-4.5	A
	T_A=70°C		3.5	-3.5	
Pulsed Drain Current [C]		I_{DM}	20	-20	
Power Dissipation [B]	T_A=25°C	P_D	2.1	2.1	W
	T_A=70°C		1.3	1.3	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	-55 to 150	°C

Thermal Characteristics: N-channel

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	50	60	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		80	100	°C/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	30	40	°C/W

Thermal Characteristics: P-channel

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	50	60	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		80	100	°C/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	30	40	°C/W

N-channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±10V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250µA	0.7	1.05	1.5	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V	20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=4.5A		42	52	mΩ
		T_J=125°C		66	82	
		V_{GS}=4.5V, I_D=3A		47	60	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=4.5A		15		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.75	1	V
I_S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		245		pF
C_{oss}	Output Capacitance			35		pF
C_{rss}	Reverse Transfer Capacitance			20		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		5.3		Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=4.5A		5.7	10	nC
Q_g(4.5V)	Total Gate Charge			2.6	5	nC
Q_{gs}	Gate Source Charge			0.5		nC
Q_{gd}	Gate Drain Charge			1		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=3.3Ω, R_{GEN}=3Ω		2		ns
t_r	Turn-On Rise Time			3.5		ns
$t_{D(off)}$	Turn-Off DelayTime			22		ns
t_f	Turn-Off Fall Time			3.5		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=4.5A, dI/dt=500A/µs		6.5		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=4.5A, dI/dt=500A/µs		7.5		nC

A. The value of R_{qJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using ≤ 10s junction-to-ambient thermal resistance.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initialT_J=25° C.
D. The R_{qJA} is the sum of the thermal impedance from junction to lead R_{qJL} and lead to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300ms pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. The maximum current rating is package limited.

N-channel TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

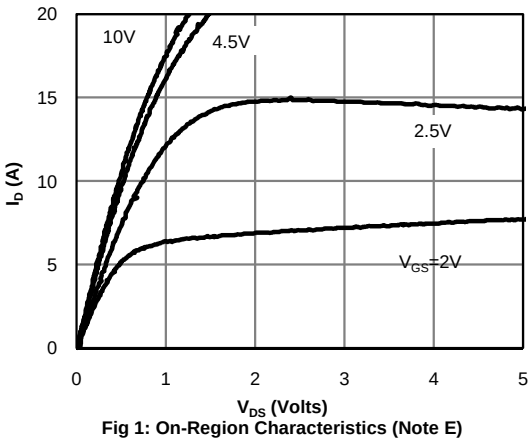


Fig 1: On-Region Characteristics (Note E)

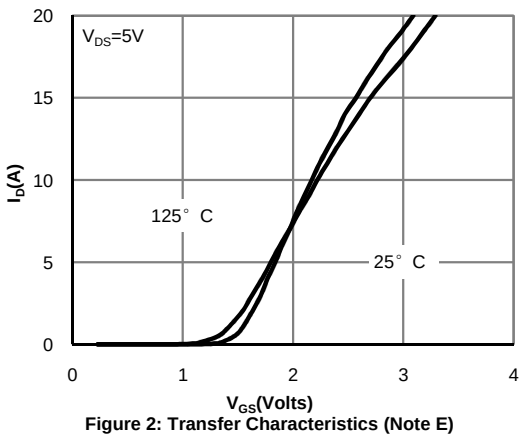


Figure 2: Transfer Characteristics (Note E)

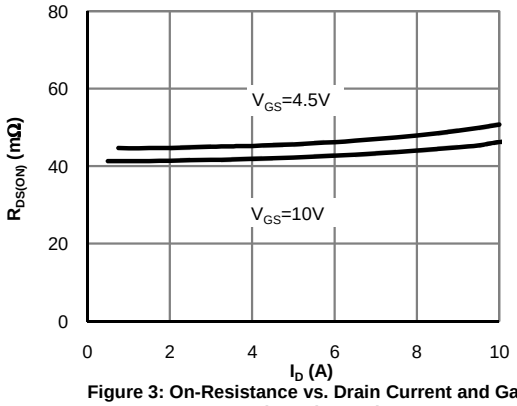


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

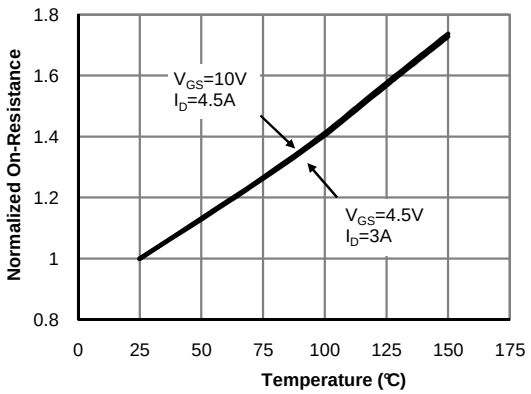


Figure 4: On-Resistance vs. Junction Temperature (Note E)

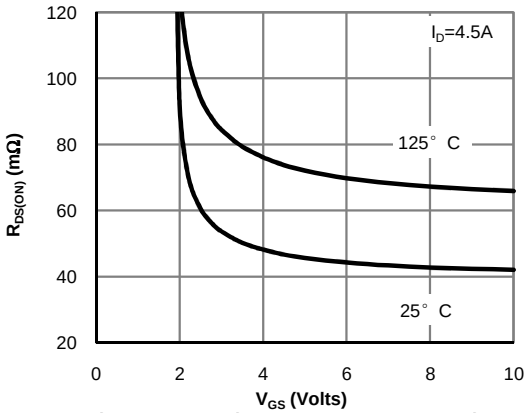


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

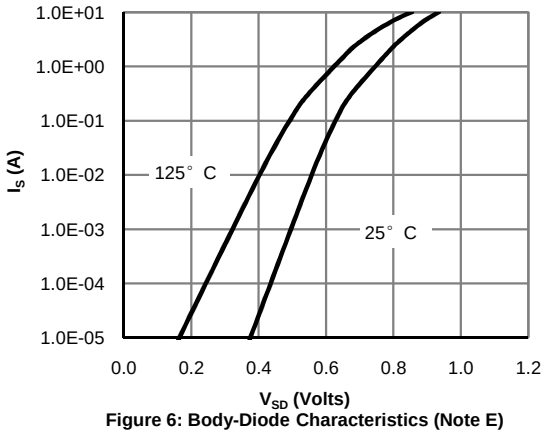


Figure 6: Body-Diode Characteristics (Note E)

N-channel TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

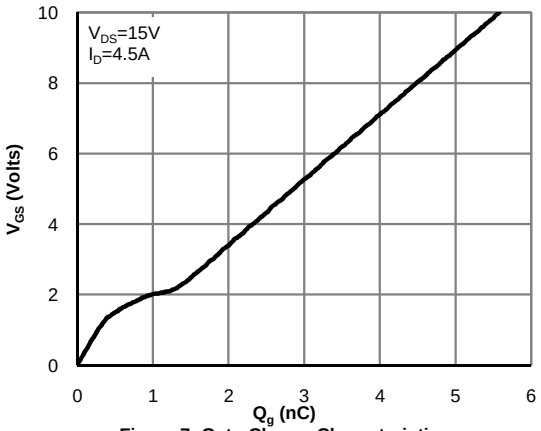


Figure 7: Gate-Charge Characteristics

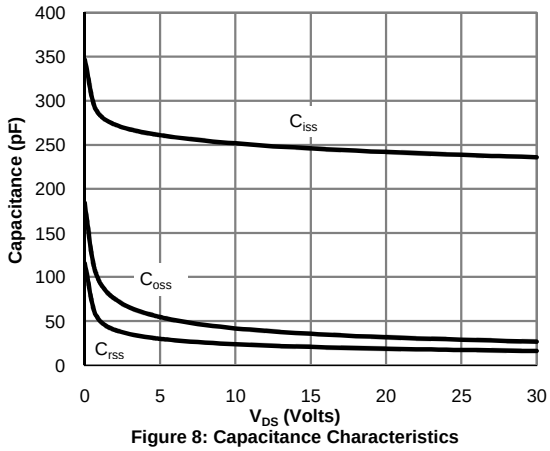


Figure 8: Capacitance Characteristics

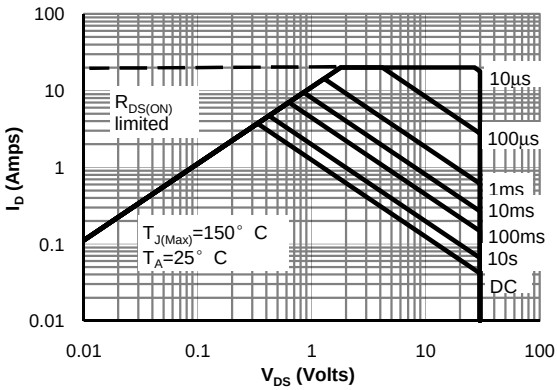


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

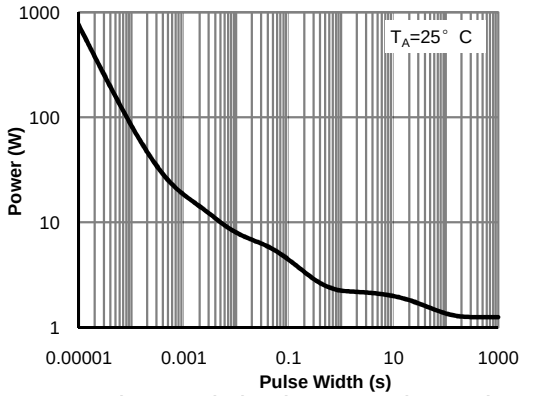


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

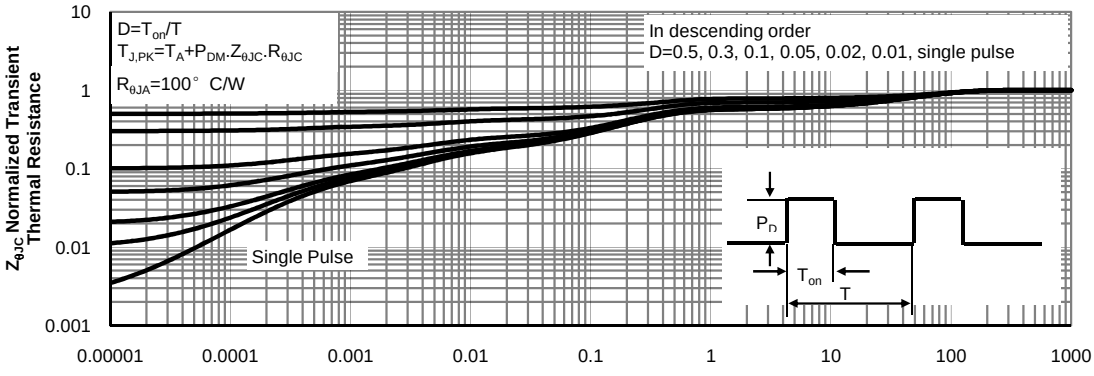
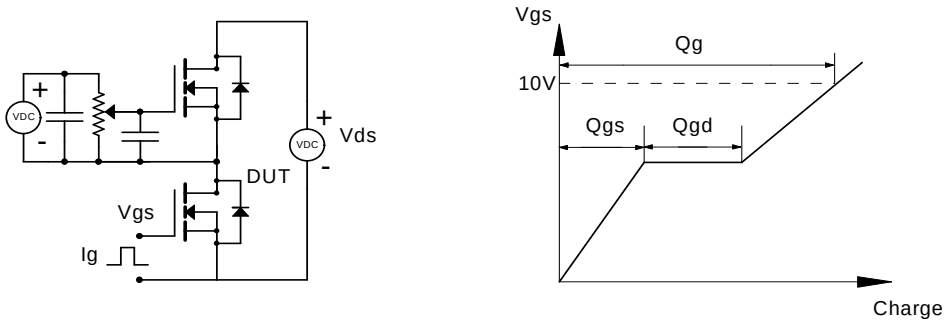
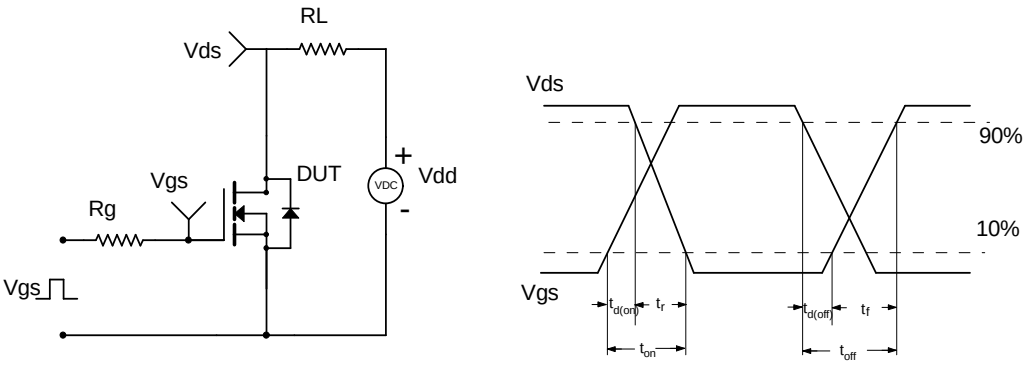


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

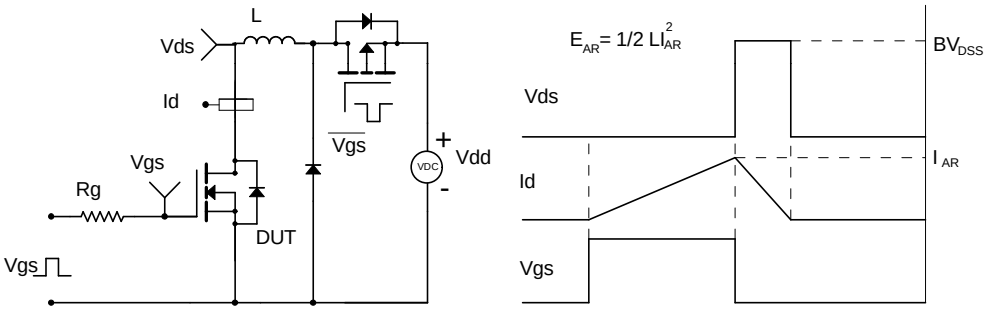
Gate Charge Test Circuit & Waveform



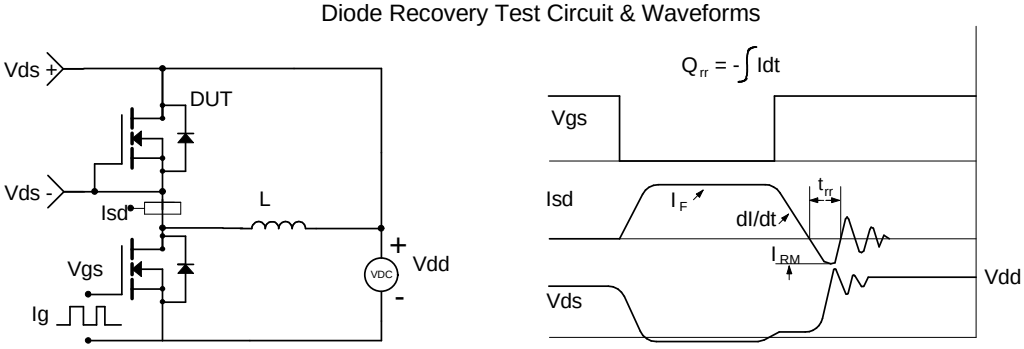
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



P-channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0V			-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250µA	-1.3	-1.8	-2.3	V
$I_{D(ON)}$	On state drain current	V_{GS}=-10V, V_{DS}=-5V	-20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V, I_D=-4.5A		56	68	mΩ
		T_J=125°C		79	96	
		V_{GS}=-4.5V, I_D=-3A		80	100	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-4.5A		8		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V		-0.78	-1	V
I_S	Maximum Body-Diode Continuous Current				-2.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-15V, f=1MHz		290		pF
C_{oss}	Output Capacitance			60		pF
C_{rss}	Reverse Transfer Capacitance			40		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		16		Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=-10V, V_{DS}=-15V, I_D=-4.5A		5.8	10	nC
Q_g(4.5V)	Total Gate Charge			2.8	6	nC
Q_{gs}	Gate Source Charge			1.1		nC
Q_{gd}	Gate Drain Charge			1.3		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-10V, V_{DS}=-15V, R_L=3.3Ω, R_{GEN}=3Ω		6		ns
t_r	Turn-On Rise Time			5		ns
$t_{D(off)}$	Turn-Off DelayTime			21		ns
t_f	Turn-Off Fall Time			9		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-4.5A, dI/dt=500A/µs		10		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-4.5A, dI/dt=500A/µs		20		nC

A. The value of R_{qJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using ≤ 10s junction-to-ambient thermal resistance.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initialT_J=25° C.
D. The R_{qJA} is the sum of the thermal impedance from junction to lead R_{qJL} and lead to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300ms pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. The maximum current rating is package limited.

P-channel TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

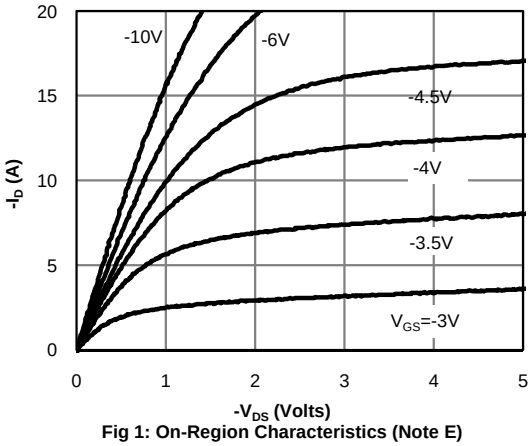


Fig 1: On-Region Characteristics (Note E)

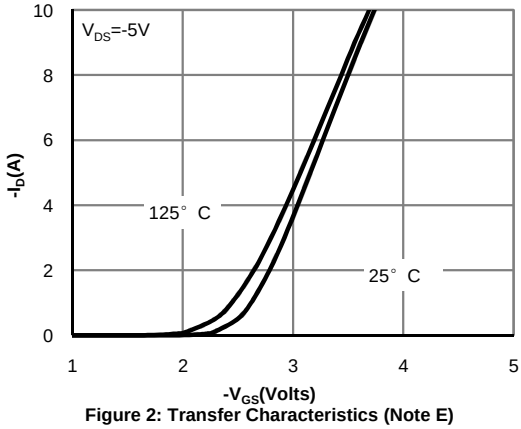


Figure 2: Transfer Characteristics (Note E)

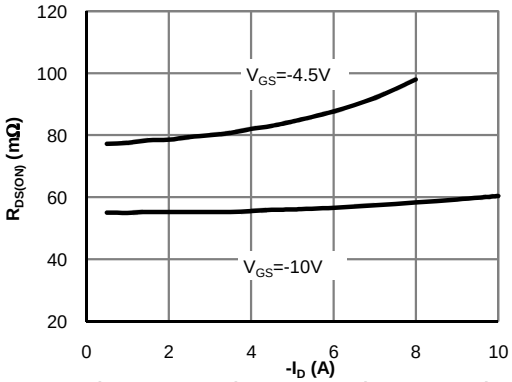


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

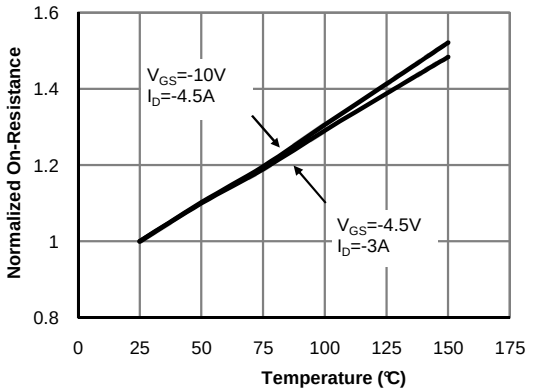


Figure 4: On-Resistance vs. Junction Temperature (Note E)

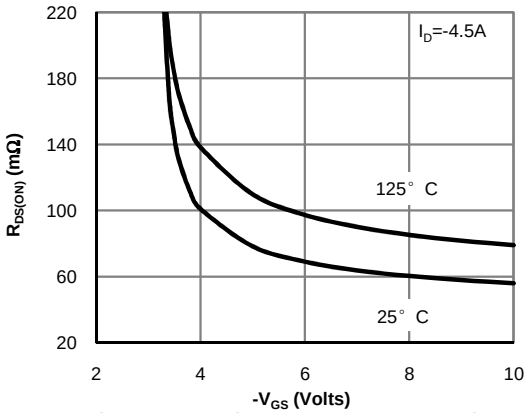


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

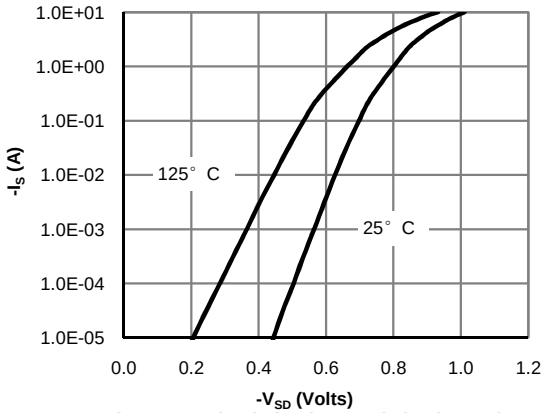


Figure 6: Body-Diode Characteristics (Note E)

P-channel TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

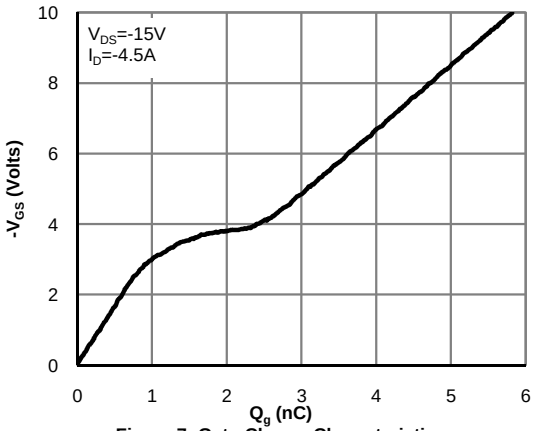


Figure 7: Gate-Charge Characteristics

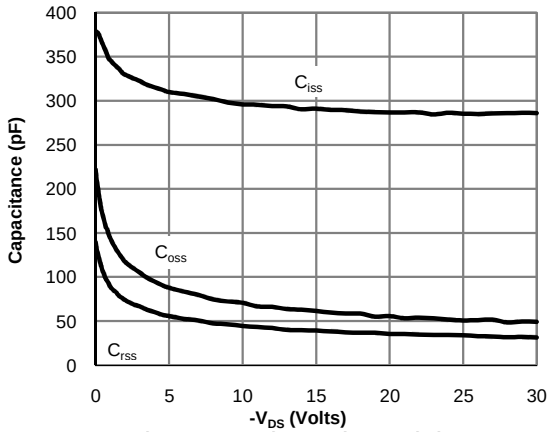


Figure 8: Capacitance Characteristics

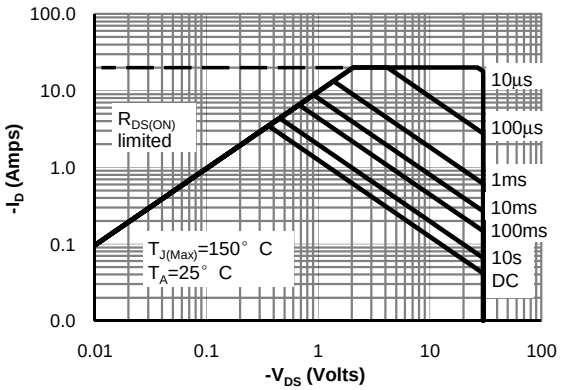


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

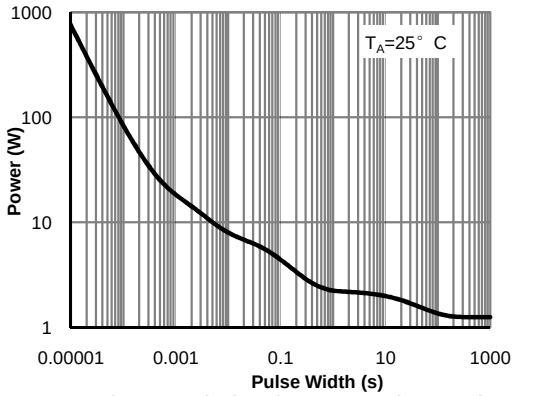


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

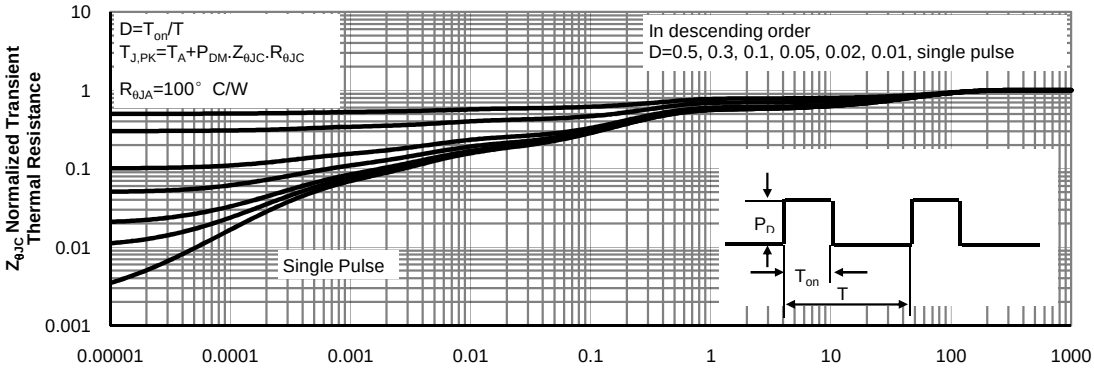
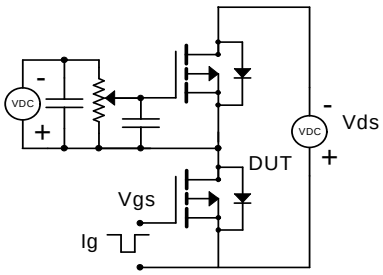
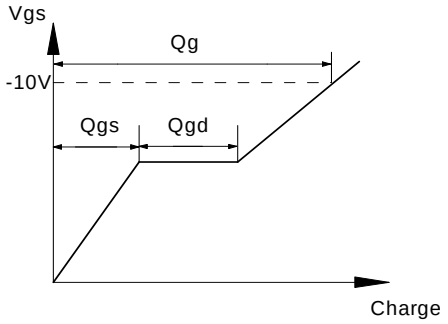


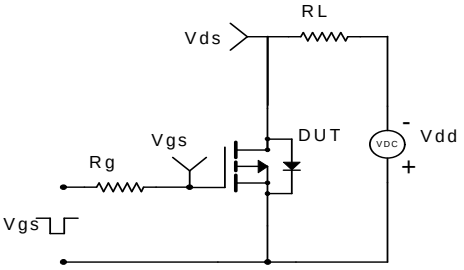
Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

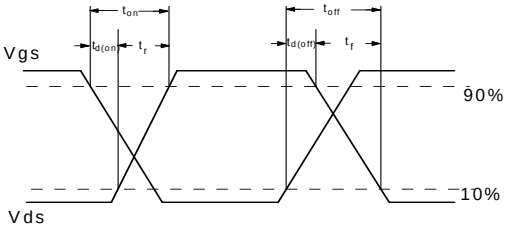
Gate Charge Test Circuit & Waveform



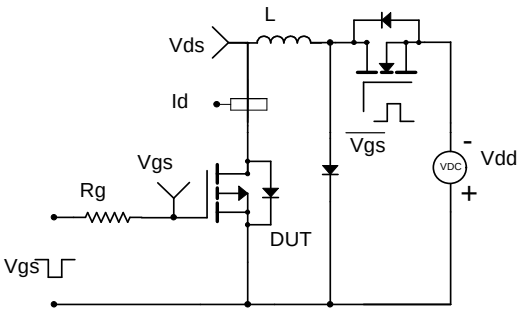


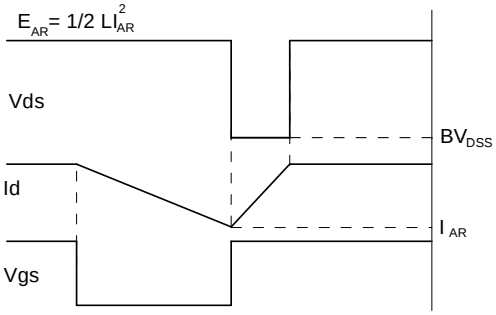
Resistive Switching Test Circuit & Waveforms





Unclamped Inductive Switching (UIS) Test Circuit & Waveforms





Diode Recovery Test Circuit & Waveforms